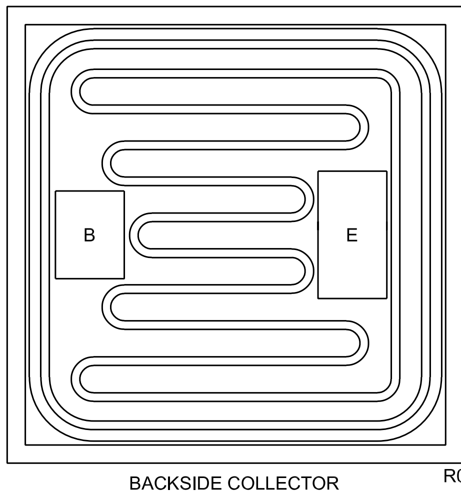
Central™
Semiconductor Corp.

PROCESS CP734V
Small Signal Transistors
PNP - Chopper Transistor Chip

PROCESS DETAILS

Process	Epitaxial Planar
Die Size	31.5 x 31.5 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Area	4.7 x 6.7 MILS
Emitter Bonding Pad Area	4.7 x 8.7 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

Geometry



GROSS DIE PER 4 INCH WAFER
11,210

PRINCIPAL DEVICE TYPES
CMPT404A
MPS404A

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

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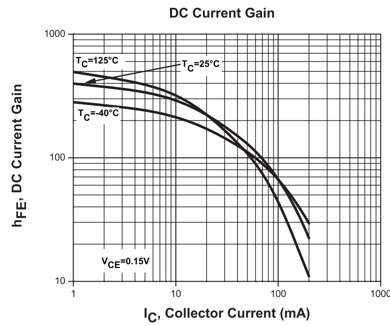
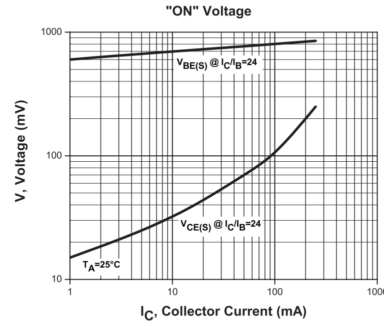
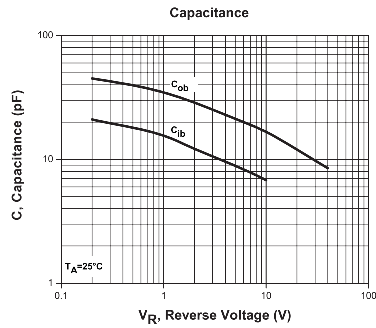
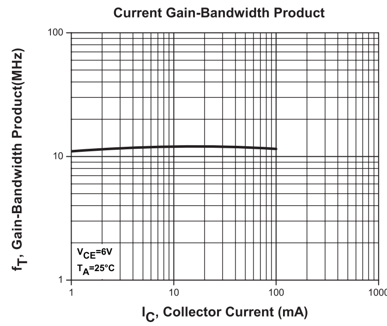
PROCESS CP734V

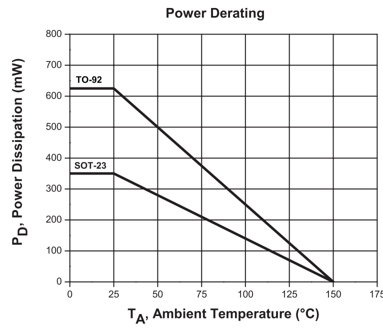
Typical Electrical Characteristics











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